

Please type a plus sign (+) inside this box → +

O I P E
DEC 16 2002

PTO/SB/08B (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

2

of

2

Complete if Known

Application Number	09/747,779
Filing Date	December 22, 2000
First Named Inventor	Kim, Hong Koo
Group Art Unit	1765
Examiner Name	Unassigned
Attorney Docket Number	000939-073311US

RECEIVED
TECHNOLOGY CENTER 2800
DEC 18 2002

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
HD P	AA	BASIT et al., "Growth of highly oriented Pb(Zr, Ti)O ₃ films on MgO-buffered oxidized Si substrates and its application to ferroelectric nonvolatile memory field-effect transistors," <u>Applied Physics Letters</u> , 73(26):3941-3943 (1998).	
HD P	AB	BASIT et al., "Temperature dependence of lead loss in r.f. magnetron sputtering of a stoichiometric Pb(Zr, Ti)O ₃ target," <u>Thin Solid Films</u> , 302:155-161 (1997).	
HD P	AC	BASIT et al., "Crystallization of Pb(Zr, Ti)O ₃ films prepared by rf magnetron sputtering with a stoichiometric oxide target," <u>J. Vac. Sci. Technol.</u> , A 13(4):2214-2220 (1995).	
HD P	AD	BUHAY et al., "Pulsed laser deposition and ferroelectric characterization of bismuth titanate films," <u>Appl. Phys. Lett.</u> , 58(14):1470-1472 (1991).	
MSP	AE	DAX, M., eds., "The Non-Volatile Memory Challenge," <u>Semiconductor International</u> , September 1997, pages 84-92.	
HD P	AF	HAN et al., "SrBi ₂ Ta ₂ O ₉ memory capacitor on Si with a silicon nitride buffer," <u>Applied Physics Letters</u> , 72(10):1185-1186 (1998).	
HD P	AG	HIRAI et al., "Formation of Metal / Ferroelectric / Insulator / Semiconductor Structure with a CeO ₂ Buffer Layer," <u>Jpn. J. Appl. Phys.</u> , 33(9B)pt. 1: 5219-5222 (1994).	
HD P	AH	KIM et al., "Memory window of Pt-Bi ₂ Ta ₂ O ₉ /CeO ₂ /Si structure for metal ferroelectric insulator semiconductor field effect transistor," <u>Appl. Phys. Lett.</u> , 71(24):3507-3509 (1997).	
HD P	AI	MILLER et al., "Physics of the ferroelectric nonvolatile memory field effect transistor," <u>J. Appl. Phys.</u> , 72(12):5999-6010 (1992).	
HD P	AJ	NASHIMOTO et al., "Epitaxial growth of MgO on GaAs(001) for growing epitaxial BaTiO ₃ thin films by pulsed laser deposition," <u>Appl. Phys. Lett.</u> , 60(10):1199-1201 (1992).	
HD P	AK	ROST et al., "Ferroelectric switching of a field-effect transistor with a lithium niobate gate insulator," <u>Appl. Phys. Lett.</u> , 59(27):3654-3656 (1991).	
HD P	AL	SINHAROY et al., "Growth and characterization of ferroelectric BaMgF ₄ films," <u>J. Vac. Sci. Technol.</u> , A9(3):409-413 (1991).	
HD P	AM	TOKUMITSU et al., "Nonvolatile Memory Operations of Metal-Ferroelectric-Insulator-Semiconductor (MFIS) FET's Using PLZT/STO/Si(100) Structures," <u>IEEE Electric Device Letters</u> , 18(4):160-162 (1997).	
HD P	AN	WANG et al., "Deposition of in-plane textured MgO on amorphous Si ₃ N ₄ substrates ion-beam-assisted deposition and comparisons with ion-beam-assisted deposited yttria-stabilized-zirconia," <u>Appl. Phys. Lett.</u> , 71(20):2955-2957 (1997).	
HD P	AO	WU, Shu-Yau, "A New Ferroelectric Memory Device, Metal-Ferroelectric-Semiconductor Transistor," <u>IEEE Transactions on Electron Devices</u> , ED-21(8):499-504 (1974).	

Examiner Signature

Date Considered

2/20/2003

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

PA 3193129 v1

Please type a plus sign (+) inside this box

+



PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person is required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

2

Complete If Known	
Application Number	09/747,779
Filing Date	December 22, 2000
First Named Inventor	Kim, Hong Koo
Group Art Unit	1765
Examiner Name	Unassigned
Attorney Docket Number	000939-073311US

9/20 DS
8 Mer A
1-6-02

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Signature		Date Considered	
-------------------------------	--	----------------------------	--

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

PA 3193129 v1